

ABSTRACT OF THE DISCLOSURE

A multi-finger type electrostatic discharge protection circuit is disclosed. In an NMOS type ESD protection circuit, a pair of gates are formed in parallel with each other in one of multiple active regions so as to enable all the gate fingers in the active regions to perform npn bipolar operations uniformly. The present invention discharges an ESD pulse effectively by forming one or more additional n⁺ (or p⁺) type active regions, which are connected to Vcc (or Vss), between respective active regions.